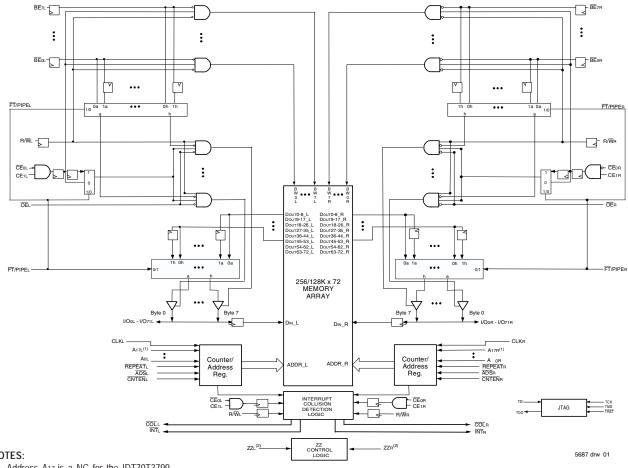


HIGH-SPEED 2.5V 70T3719/99M 256/128K x 72 **SYNCHRONOUS DUAL-PORT STATIC RAM** WITH 3.3V OR 2.5V INTERFACE

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed data access - Commercial: 3.6ns (166MHz) 4.2ns (133MHz)(max.)
 - Industrial: 4.2ns (133MHz) (max.)
- Selectable Pipelined or Flow-Through output mode
- Counter enable and repeat features
- Dual chip enables allow for depth expansion without additional logic
- Interrupt and Collision Detection Flags
- Full synchronous operation on both ports
 - 6ns cycle time, 166MHz operation (23.9Gbps bandwidth)
 - Fast 3.6ns clock to data out
 - Self-timed write allows fast cycle time
- Functional Block Diagram

- 1. 7ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 166MHz
- Data input, address, byte enable and control registers
- Separate byte controls for multiplexed bus and bus matching compatibility
- Dual Cycle Deselect (DCD) for Pipelined Output Mode
- 2.5V (±100mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- ٠ Industrial temperature range (-40°C to +85°C) is available at 133MHz
- Available in a 324-pin Green Ball Grid Array (BGA)
- Includes JTAG Functionality
- Green parts available, see ordering information



NOTES:

- Address A17 is a NC for the IDT70T3799.
- The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode.

70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Description:

The IDT70T3719/99M is a high-speed 256K/128K x 72 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70T3719/99M has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70T3719/99M can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) is at 2.5V.

70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Pin Configuration (2,3,4,5)

70T3719/99M BBG324⁽⁶⁾

324-Pin BGA Top View⁽⁷⁾

06/27/05	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	
A	I/O39R	VO38R	VO37R	I/O36R	COL	A15L	A12L	A8L	BE 7L	BE 2L	CE1L	ADSL	A6L	A1L	I/O32R	VO33R	I/O34R	I/O35r	A
В	VO39L	I/O38L	VO37L	VO36L	TDO	A17L ⁽¹⁾	A13L	A10L	BE 6L	BE 5L	BE 1L	ŌĒL	REPEATL	Aol	VO32L	VO33L	VO34L	VO35L	В
С	I/O40r	VO41R	VO42R	I/O43R	ĪNT	A16L	A11L	A7L	BEOL	CEOL	R/WL		A4L	A3L	VO31R	I/O30R	I/O29R	VO28R	С
D	I/O40L	1/041L	VO42L	VO43L	TDI	NC	A14L	A9L	BE 4L	BE 3L	CLKL	A5L	A2L	ZZL	VO31L	VO30L	VO29L	VO28L	D
E	VO47R	VO46R	VO45R	VO44R	PL/FTL	Vdd	Vddql	Vddqr	Vddqr	VDDQL	Vddql	Vddqr	Vddqr	OPTL	VO24R	VO25R	I/O26R	VO27R	E
F	VO47L	I/O46L	I/O45L	VO44L	Vdd	Vdd	VDDQL	Vss	Vss	Vss	Vdd	Vdd	Vdd	Vdd	VO24L	VO25L	VO26L	VO27L	F
G	VO48R	VO49R	1/O50R	I/O 51R	Vddqr	VDDQR	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	VDDQR	I/O23R	VO22R	I/O21r	I/O20R	G
Η	1/O48L	1/049L	I/O50L	VO 51L	Vddql	VDDQL	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	VDDQL	VO23L	VO22L	VO21L	I/O20L	Н
J	I/O _{55R}	1/054R	I/O53R	VO52R	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	1/016R	I/O17R	I/O18R	VO19R	J
К	1/O55L	1/O54L	1/O53l	VO52L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	1/O16L	VO17L	VO _{18L}	1/O19L	K
L	1/056r	VO57R	VO58R	VO59R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	VO15R	I/014R	I/O13R	VO12R	L
М	1/O56L	1/057L	1/058L	VO59L	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vddal	Vddql	VO15L	VO14L	VO _{13L}	VO12L	М
Ν	VO63R	VO62R	VO61R	1/060R	Vddqr	VDDQR	VDDQL	VDDQL	Vss	Vss	Vdd	Vddqr	Vddqr	Vddqr	I/O8r	VO9R	I/O10R	VO11R	Ν
Р	1/063L	1/062L	1/061L	VO60L	ZZr	™S	Vdd	Vdd	Vdd	VDDQL	Vddql	Vdd	Vdd	OPTr	I/O8L	VO9L	VO10L	I/O 11L	Р
R	VO64R	VO65R	1/066r	1/067R	COLR	A17R ⁽¹⁾	A12R	A9R	BE 4R	CEOR	ŌĒr	A6R	A2R	A1R	V07r	VO6R	VO5r	VO4R	R
Т	1/064L	1/065L	1/066L	VO67L	PL/ FT r	A16R	A13R	A7r	BE 7R	BE 3R	CE1R	ADSR	A4R	Aor	I/O7L	I/O6L	I/O5L	VO4L	Т
U	V071R	1/O70r	1/069R	I/068R	TCK	INT r	A14R	A10R	BE _{2R}	BE 6R	BE 1R	R/Wr	REPEATR	A3r	I/Oor	VO1R	VO₂r	I/O 3R	U
V	I ∕O71L	I/O70L	1/069L	1/068L	TRST	NC	A15R	A11r	Aßr	BE 5R	BEOR	CLKr	CNTENR	A5r	I/Ool	I/O1L	I/O2L	VO3L	V
I	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	
																		5687 tbl 01	

NOTES:

1. Pin is a NC for IDT70T3799.

2. All VDD pins must be connected to 2.5V power supply.

3. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VDD (2.5V), and 2.5V if OPT pin for that port is set to Vss (0V).

4. All Vss pins must be connected to ground supply.

5. Package body is approximately 19mm x 19mm x 1.76mm, with 1.0mm ball-pitch.

6. This package code is used to reference the package diagram.

7. This text does not indicate orientation of the actual part-marking.

70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Pin Names

Left Port	Right Port	Names			
CE0L, CE1L	CEOR, CE1R	Chip Enables (Input) ⁽⁶⁾			
R/WL	R/WR	Read/Write Enable (Input)			
ŌĒL	ŌĒR	Output Enable (Input)			
Aol - A17L ⁽⁵⁾	Aor - A17r ⁽⁵⁾	Address (Input)			
1/Ool - 1/071L	1/O0r - 1/071r	Data Input/Output			
CLKL	CLKr	Clock (Input)			
PL/ FT L	PL/FTR	Pipeline/Flow-Through (Input)			
ADSL	ADSR	Address Strobe Enable (Input)			
	CNTEN R	Counter Enable (Input)			
REPEATL	REPEATR	Counter Repeat ⁽³⁾			
BEOL - BE7L	BEOR - BE7R	Byte Enables (9-bit bytes) (Input) ⁽⁶⁾			
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾ (Input			
OPTL	OPTR	Option for selecting VDDOX ^(1,2) (Input)			
ZZL	ZZR	Sleep Mode pin ⁽⁴⁾ (Input)			
	VDD	Power (2.5V) ⁽¹⁾ (Input)			
	Vss	Ground (0V) (Input)			
	TDI	Test Data Input			
	TDO	Test Data Output			
	ТСК	Test Logic Clock (10MHz) (Input)			
	TMS	Test Mode Select (Input)			
=	TRST	Reset (Initialize TAP Controller) (Input)			
ĪNT∟	ĪNTR	Interrupt Flag (Output)			
		Collision Alert (Output)			

5687 tbl 02

Industrial and Commercial Temperature Ranges

NOTES:

- 1. VDD, OPTx, and VDDDx must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to Vob (2.5V), then that port's I/Os and controls will operate at 3.3V levels and Vobox must be supplied at 3.3V. If OPTx is set to Vss (0V), then that port's I/Os and address controls will operate at 2.5V levels and Vobox must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

 When REPEAT x is asserted, the counter will reset to the last valid address loaded via ADSx.

4. The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode. It is recommended that boundary scan not be operated during sleep mode.

- 5. Address A17x is a NC for the IDT70T3799M.
- Chip Enables and Byte Enables are double buffered when PL/FT = VIH, i.e., the signals take two cycles to deselect.

70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Truth Table I—Read/Write and Enable Control (1,2,3,4,5)

ŌĒ	CLK	CE ₀	CE1	Byte Enables	R/₩	ZZ	I/O Operation ⁽⁶⁾	MODE	
Х	1	Н	Х	All BE = X	Х	L	All Bytes= High-Z	Deselected: Power Down	
Х	¢	Х	L	All \overline{BE} = X	Х	L	All Bytes = High-Z	Deselected: Power Down	
Х	†	L	Н	All BE = H	Х	L	All Bytes = High-Z	All Bytes Deselected	
Х	¢	L	Н	$\overline{BE}n = L$, All other $\overline{BE} = H$	L	L	Byten = DiN, All other Bytes = High-Z	Write to Byte X Only	
Х	↑	L	Н	$\overline{BE}_{4-7} = L, \ \overline{BE}_{0-3} = H$	L	L	Byte4-7 = DIN, Byteo-3 = High-Z	Write to Lower Bytes Only	
Х	1	L	Н	$\overline{BE}_{4-7} = H, \ \overline{BE}_{0-3} = L$	L	L	Byte₄.7 = High-Z, Byte₀.3 = Dℕ	Write to Upper Bytes Only	
Х	1	L	Н	$\overline{BE}_{0-7} = L$	L	L	Byteo.7 = DIN	Write to All Bytes	
L	↑	L	Н	$\overline{BE}n = L$, All other $\overline{BE} = H$	Н	L	Byten = Dout, All other Bytes = High-Z	Read Byte X Only	
L	↑	L	Н	$\overline{BE}_{4-7} = L, \ \overline{BE}_{0-3} = H$	Н	L	Byte4.7 = Dout, Byte0.3 = High-Z	Read Lower Bytes Only	
L	↑	L	Н	$\overline{BE}_{4-7} = H, \ \overline{BE}_{0-3} = L$	Н	L	Byte4-7 = High-Z, Byteo-3 = Dout	Read Upper Bytes Only	
L	↑	L	Н	All BE = L	Н	L	All Bytes = Dout	Read All Bytes	
Н	Х	Х	Х	All BE = X	Х	L	All Bytes = High-Z	Outputs Disabled	
Х	Х	Х	Х	All BE = X	Х	Н	All Bytes = High-Z	Sleep Mode	

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = X$.

3. OE and ZZ are asynchronous input signals.

4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

5. For the examples shown here, BEn may correspond to any of the eight byte enable signals.

Previous Internal Address Internal ADS⁽⁴⁾ Address Address Used CLK CNTEN REPEAT^(4,6) I/O⁽³⁾ MODE An Х An Υ L Х н Di/o(n) External Address Used L⁽⁵⁾ Counter Enabled-Internal Address generation An + 1 Н н Х An Υ Di/o(n+1) Х An + 1 An + 1 ተ Н Н н Di/o(n+1) Enabled Address Blocked-Counter disabled (An + 1 reused) Х Counter Set to last valid ADS load Х Х Х An ተ L Di/o(n)

Truth Table II—Address Counter Control^(1,2)

NOTES:

1. "H" = VIH. "L" = VIL. "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CE0, CE1, BEn and OE.

3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the data out will be delayed by one cycle.

4. ADS and REPEAT are independent of all other memory control signals including CE0, CE1 and BEn.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE₀, CE1, BEn.

6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.

5687 tbl 04

5687 tbl 03

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	2.5V <u>+</u> 100mV
Industrial	-40°C to +85°C	0V	2.5V <u>+</u> 100mV
			5687 tbl 05

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions with VDDQ at 2.5V

Parameter	Min.	Тур.	Max.	Unit
Core Supply Voltage	2.4	2.5	2.6	V
I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	V
Ground	0	0	0	V
Input High Volltage (Address, Control & Data I/O Inputs) ⁽³⁾	1.7		Vddq + 100mV ⁽²⁾	v
Input High Voltage - JTAG	1.7		VDD + 100mV ⁽²⁾	v
Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		VDD + 100mV ⁽²⁾	V
Input Low Voltage	-0.3 ⁽¹⁾		0.7	V
Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	V
	I/O Supply Voltage ⁽³⁾ Ground Input High Voltage (Address, Control & Data I/O Inputs) ⁽³⁾ Input High Voltage - JTAG Input High Voltage - ZZ, OPT, PIPE/FT Input Low Voltage Input Low Voltage -	I/O Supply Voltage ⁽³⁾ 2.4 Ground 0 Input High Voltage (Address, Control & Data I/O Inputs) ⁽³⁾ 1.7 Input High Voltage - JTAG 1.7 Input High Voltage - JTAG 1.7 Input High Voltage - JTAG VDD - 0.2V Input Low Voltage - Input Low Voltage - Data I/O -0.3 ⁽¹⁾	I/O Supply Voltage2.42.5Ground00Input High Voltage (Address, Control & Data I/O Inputs)1.7Input High Voltage - JTAG1.7Input High Voltage - ZZ, OPT, PIPE/FTVDD - 0.2VInput Low Voltage - Input Low Voltage - 0.2(1)0.2(1)	I/O Supply Voltage ⁽³⁾ 2.4 2.5 2.6 Ground 0 0 0 Input High Voltage (Address, Control & Data I/O Inputs) ⁽³⁾ 1.7 VDD0 + 100mV ⁽²⁾ Input High Voltage - JTAG 1.7 VDD + 100mV ⁽²⁾ Input High Voltage - JTAG 1.7 VDD + 100mV ⁽²⁾ Input High Voltage - JTAG VDD - 0.2V VDD + 100mV ⁽²⁾ Input Low Voltage -0.3 ⁽¹⁾ 0.7 Input Low Voltage - 0.2 ⁽¹⁾ 0.2

NOTES:

---- --

- 1. VIL (min.) = -1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.
- 2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.

3. To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to $V_{SS}(0V)$, and V_{DDOX} for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDQ at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	2.4	2.5	2.6	V
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
Vн	Input High Voltage (Address, Control &Data I/O Inputs) ⁽³⁾	2.0		Vddq + 150mV ⁽²⁾	v
VIH	Input High Voltage - JTAG	1.7		VDD + 100mV ⁽²⁾	V
VIH	Input High Voltage - ZZ, OPT, PIPE/FT	Vdd - 0.2V		$V_{DD} + 100 mV^{(2)}$	V
V⊫	Input Low Voltage	-0.3(1)		0.8	V
VIL	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	V

NOTES:

- 1. VIL (min.) = -1.0V for pulse width less than tcyc/2, or 5ns, whichever is less.
- 2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.
- To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to Vbb (2.5V), and Vbbox for that port must be supplied as indicated above.

70T3719/99M

High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Absolute Maximum Ratings ⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm (Vdd)	VDD Terminal Voltage with Respect to GND	-0.5 to 3.6	V
Vterm ⁽²⁾ (Vddq)	VDDQ Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
V _{TERM⁽²⁾ (INPUTS and I/O's)}	Input and I/O Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
TBIAS ⁽³⁾	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
ЛЛ	Junction Temperature	+150	٥C
IOUT(For VDDQ = 3.3V)	DC Output Current	50	mA
IOUT(For VDDQ = 2.5V)	DC Output Current	40	mA
			5687 tbl 0

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. This is a steady-state DC parameter that applies after the power supply has reached its nominal operating value. Power sequencing is not necessary; however, the voltage on any Input or I/O pin cannot exceed VDDo during power supply ramp up.
- 3. Ambient Temperature under DC Bias. No AC Conditions. Chip Deselected.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, F = 1.0MHz)$

Symbo	Parameter	Conditions ⁽²⁾	Мах.	Unit	
Cin	Input Capacitance	VIN = OV	15	рF	
Cout ⁽²⁾	Output Capacitance	Vout = 0V	10.5	pF	
				5687 tbl 08	

NOTES:

1. These parameters are determined by device characterization, but are not

production tested.

2. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 2.5V ± 100mV)

			70T3719/99M		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	VDDQ = Max., VIN = 0V to VDDQ		10	μA
Lu	JTAG & ZZ Input Leakage Current ^(1,2)	$V_{DD} = Max., V_{IN} = 0V$ to V_{DD}		±30	μA
Ilo	Output Leakage Current ^(1,3)	\overline{CE}_0 = Vih or CE1 = Vil, Vout = 0V to VDDQ		10	μA
Vol (3.3V)	Output Low Voltage ⁽¹⁾	IOL = +4mA, $VDDQ = Min$.		0.4	V
Voн (3.3V)	Output High Voltage ⁽¹⁾	Ioh = -4mA, Vdda = Min.	2.4		V
Vol (2.5V)	Output Low Voltage ⁽¹⁾	IOL = +2mA, $VDDQ = Min$.		0.4	V
Voн (2.5V)	Output High Voltage ⁽¹⁾	Ioh = -2mA, VDDQ = Min.	2.0		V

NOTES:

1. VDDQ is selectable (3.3V/2.5V) via OPT_pins. Refer to p.5 for details.

2. Applicable only for TMS, TDI and TRST inputs.

3. Outputs tested in tri-state mode.

5687 thl 09

70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(3)}$ (VDD = 2.5V ± 100mV)

						70T371 S10 Cor On		l66 m'l	S133 Com'l		
Symbol	Parameter	Test Condition	Versio	Version		Typ. ⁽⁴⁾ Max.		Max.	Un		
IDD	Dynamic Operating	\overline{CE}_{L} and $\overline{CE}_{R}=$ VIL,	COM'L	S	640	900	520	740			
	Current (Both Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	S		_	520	900	m		
ISB1 ⁽⁶⁾	Standby Current $\overline{CEL} = \overline{CER} = VIH$ (Both Ports - TTL $f = fMAX^{(1)}$		COM'L	S	350	460	280	380			
•	Level Inputs)		IND	S		_	280	470	m		
	Standby Current (One Port - TTL	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	500	650	400	500			
	Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S	_	_	400	620	m		
ISB3	Full Standby Current	Both Ports CEL and	COM'L	S	12	20	12	20			
	(Both Ports - CMOS Level Inputs)	$\label{eq:certain} \overline{\text{CE}}_{\text{R}} \geq \text{VDDQ} - 0.2\text{V}, \ \text{Vin} \geq \text{VDDQ} - 0.2\text{V} \\ \text{or Vin} \leq 0.2\text{V}, \ \text{f} = 0^{(2)} \\ \end{array}$	IND	S		_	12	25	m		
ISB4 ⁽⁶⁾	Full Standby Current	$\overline{CE}^*A^* \leq 0.2V$ and $\overline{CE}^*B^* \geq VDDQ - 0.2V^{(5)}$	COM'L	S	500	650	400	500			
	(One Port - CMOS Level Inputs)	$\label{eq:VIN_expansion} \begin{array}{l} \text{VIN} \geq \text{VDDQ} \ \text{-} \ 0.2 \text{V} \ \text{or} \ \text{VIN} \leq 0.2 \text{V} \\ \text{Active Port, Outputs Disabled, } f = f\text{MAX}^{(1)} \end{array}$	IND	S			400	620	m		
lzz	Sleep Mode Current	ZZL = ZZR = VIH	COM'L	S	12	20	12	20			
	(Both Ports - TTL Level Inputs)	f=fMAX ⁽¹⁾	IND	S	_		12	25	m		

NOTES:

1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS".

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. VDD = 2.5V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 30mA (Typ).

5. $\overline{CE}x = V_{IL}$ means $\overline{CE}_{OX} = V_{IL}$ and $CE_{IX} = V_{IH}$ $\overline{CE}x = V_{IH}$ means $\overline{CE}_{OX} = V_{IH}$ or $CE_{IX} = V_{IL}$

 $\begin{array}{l} \overline{CE}x \leq 0.2V \text{ means } \overline{CE}x \leq 0.2V \text{ and } CE1x \geq V\text{DD} + 0.2V \\ \overline{CE}x \geq V\text{DD} + 0.2V \text{ means } \overline{CE}x \geq V\text{DD} + 0.2V \text{ or } CE1x + 0.2V \\ \end{array}$

"X" represents "L" for left port or "R" for right port.

6. ISB1, ISB2 and ISB4 will all reach full standby levels (ISB3) on the appropriate port(s) if ZZL and/or ZZR = VIH.

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AC Test Conditions (VDDQ - 3.3V/2.5V)

Input Pulse Levels (Address & Controls)	GND to 3.0V/GND to 2.4V			
Input Pulse Levels (I/Os)	GND to 3.0V/GND to 2.4V			
Input Rise/Fall Times	2ns			
Input Timing Reference Levels	1.5V/1.25V			
Output Reference Levels	1.5V/1.25V			
Output Load	Figure 1			

5687 tbl 11

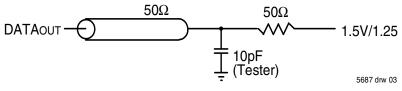
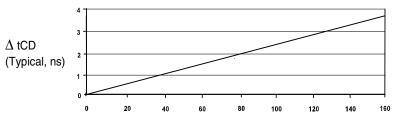


Figure 1. AC Output Test load.



 Δ Capacitance (pF) from AC Test Load 5687 drw 04

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AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) (2,3) (Vpp = 2.5V + 100mV, TA = 0°C to +70°C)

		Co	19/99M 166 om'l nly	Co	19/99M 133 m'l Ind	
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	20	—	25		ns
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	6		7.5		ns
tcн1	Clock High Time (Flow-Through) ⁽¹⁾	8		10		ns
tCL1	Clock Low Time (Flow-Through) ⁽¹⁾	8	—	10		ns
tcн2	Clock High Time (Pipelined) ⁽²⁾	2.4		3		ns
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	2.4		3		ns
tsa	Address Setup Time	1.7		1.8		ns
tha	Address Hold Time	0.5		0.5		ns
tsc	Chip Enable Setup Time	1.7		1.8		ns
tнc	Chip Enable Hold Time	0.5		0.5		ns
tsв	Byte Enable Setup Time	1.7		1.8		ns
tнв	Byte Enable Hold Time	0.5		0.5		ns
tsw	R/W Setup Time	1.7	—	1.8		ns
thw	R/W Hold Time	0.5		0.5		ns
tsp	Input Data Setup Time	1.7		1.8		ns
tнo	Input Data Hold Time	0.5	—	0.5		ns
tsad	ADS Setup Time	1.7		1.8		ns
thad	ADS Hold Time	0.5	—	0.5		ns
tscn	CNTEN Setup Time	1.7		1.8		ns
then	CNTEN Hold Time	0.5		0.5		ns
t SRPT	REPEAT Setup Time	1.7		1.8		ns
t HRPT	REPEAT Hold Time	0.5		0.5		ns
toe	Output Enable to Data Valid		4.4		4.6	ns
tolz ⁽⁴⁾	Output Enable to Output Low-Z	1		1		ns
tohz ⁽⁴⁾	Output Enable to Output High-Z	1	3.6	1	4.2	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽¹⁾		12		15	ns
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾		3.6		4.2	ns
tDC	Data Output Hold After Clock High	1		1		ns
tскнz ⁽⁴⁾	Clock High to Output High-Z	1	3.6	1	4.2	ns
tcklz ⁽⁴⁾	Clock High to Output Low-Z	1		1		ns
tins	Interrupt Flag Set Time		7		7	ns
tinr	Interrupt Flag Reset Time		7		7	ns
tcols	Collision Flag Set Time	-	3.6		4.2	ns
t COLR	Collision Flag Reset Time	—	3.6		4.2	ns
tzzsc	Sleep Mode Set Cycles	2		2		cycles
tzzrc	Sleep Mode Recovery Cycles	3		3		cycles
Port-to-Port D	- Delay	•	-			
tco	Clock-to-Clock Offset	5		6		ns
	Clock-to-Clock Offset for Collision Detection	Please r	efer to coll	sion Dotor	tion Timin	Tablo

NOTES:

1. The Pipelined output parameters (tcvc2, tcb2) apply to either or both left and right ports when FT/PIPEx = Vbb (2.5V). Flow-through parameters (tcvc1, tcb1) apply when $\overline{FT}/PIPE = V_{ss}$ (OV) for that port.

2. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPE and OPT. FT/PIPE and OPT should be treated as DC signals, i.e. steady state during operation.

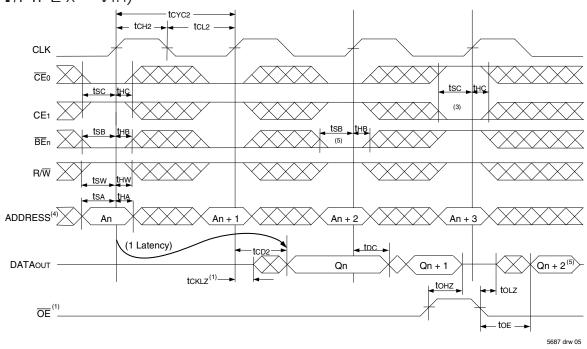
3. These values are valid for either level of VDDQ (3.3V/2.5V). See page 6 for details on selecting the desired operating voltage levels for each port.

4. Guaranteed by design (not production tested).

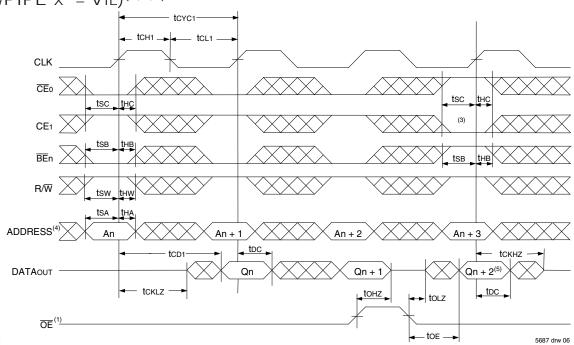
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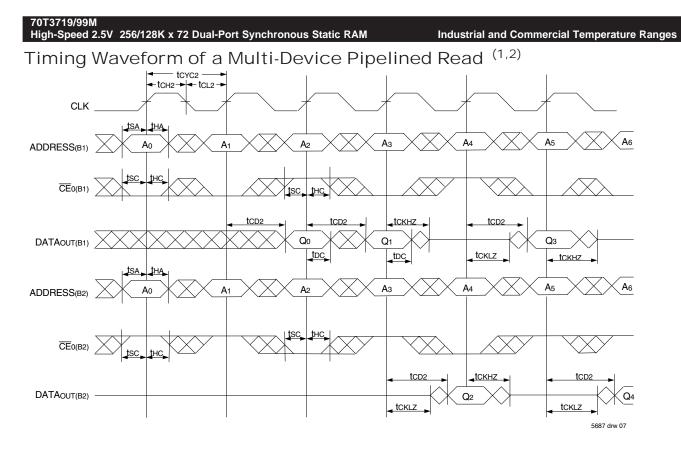


Timing Waveform of Read Cycle for Flow-through Output (FT/PIPE"x" = VIL)^(1,2,6)

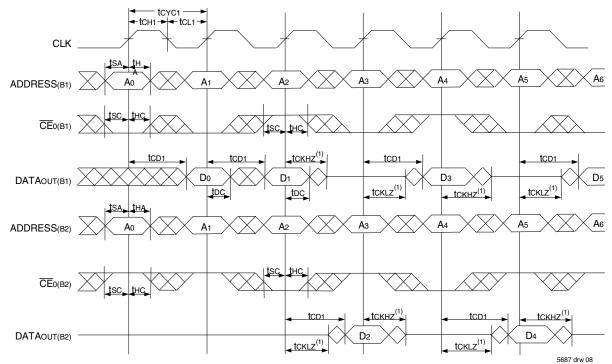


NOTES:

- 1. OE is asynchronously controlled; all other inputs depicted in the above waveforms are synchronous to the rising clock edge.
- 2. $\overline{\text{ADS}} = \text{VIL}, \overline{\text{CNTEN}} \text{ and } \overline{\text{REPEAT}} = \text{VIH}.$
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$, $\overline{BE}_n = V_{IH}$ following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If BEn was HIGH, then the appropriate Byte of DATAOUT for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.



Timing Waveform of a Multi-Device Flow-Through Read ^(1,2)

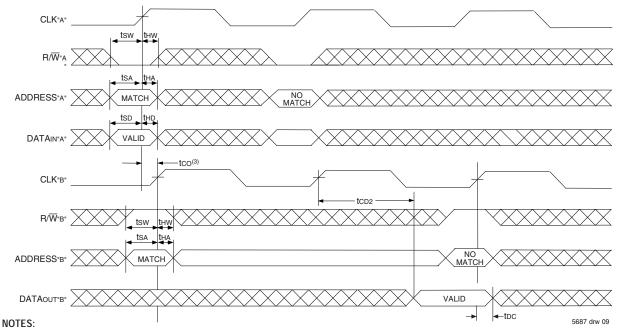


NOTES:

- 1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70T3719/99M for this waveform,
- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. $\overline{\text{BE}}$ n, $\overline{\text{OE}}$, and $\overline{\text{ADS}}$ = VIL; CE1(B1), CE1(B2), R/W, CNTEN, and REPEAT = VIH.

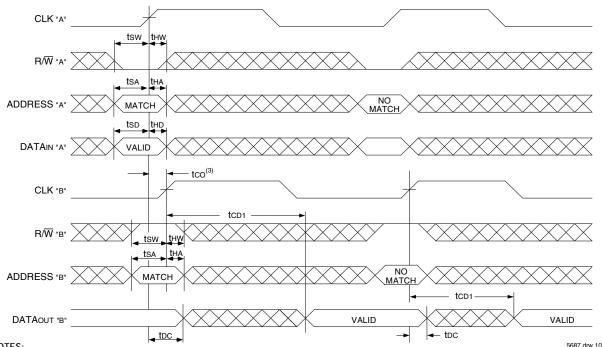
70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Timing Waveform of Left Port Write to Pipelined Right Port Read ^(1,2,4)



- 1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = V_{IL}$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- 3. If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

Timing Waveform with Port-to-Port Flow-Through Read ^(1,2,4)



NOTES:

1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = V_{IL}$; CE_{1} , \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$.

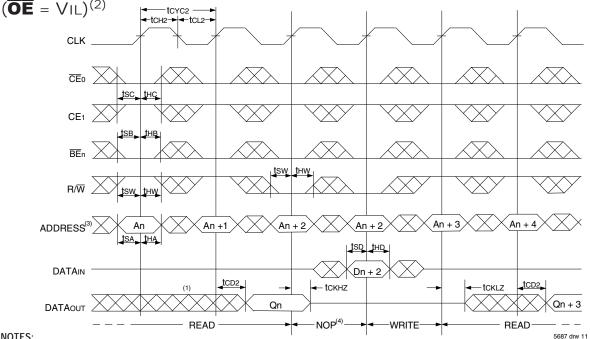
2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.

- If tco ≤ minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcyc + tcp1). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcp1).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

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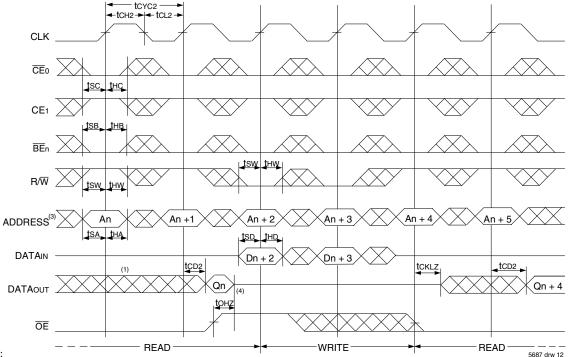
Timing Waveform of Pipelined Read-to-Write-to-Read



NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals. 2. $\overline{CE_0}$, $\overline{BE_n}$, and $\overline{ADS} = V_{IL}$; CE_1 , \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers 3. are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

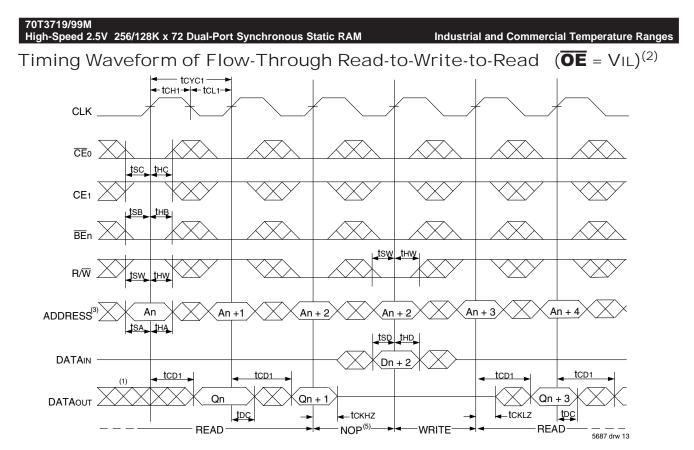
Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



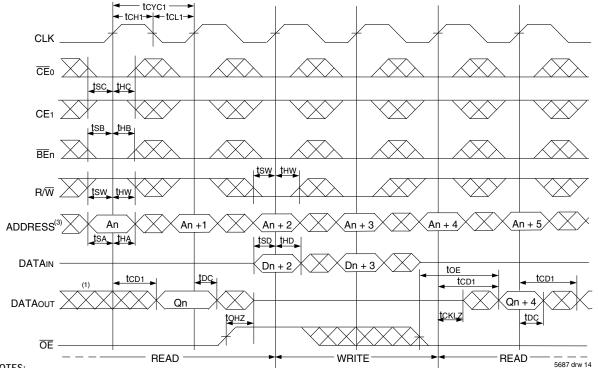
NOTES:

1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

- 2. \overline{CE}_0 , \overline{BE}_n , and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{REPEAT} = VIH$.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference 3. use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.

2. TEO, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.

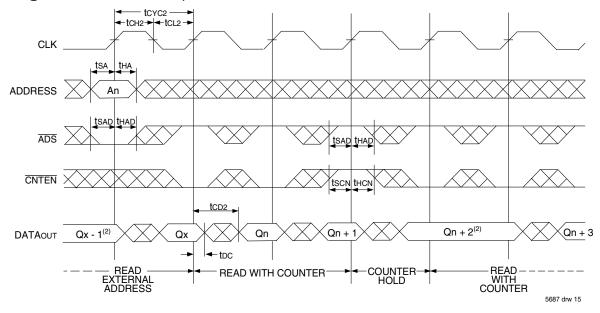
3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

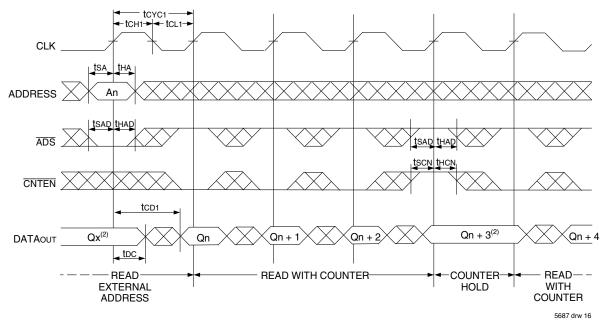
70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform of Pipelined Read with Address Counter Advance ⁽¹⁾



Timing Waveform of Flow-Through Read with Address Counter Advance $^{\left(1\right) }$



NOTES:

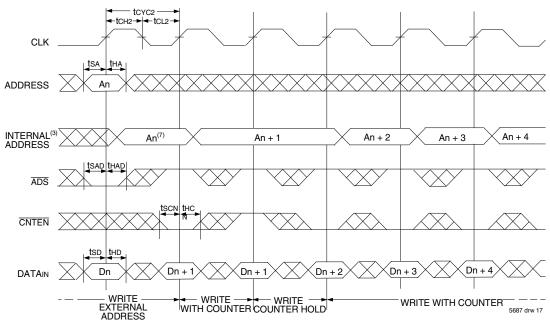
1. \overline{CE}_{0} , \overline{OE} , \overline{BE}_{n} = VIL; CE1, R/W, and \overline{REPEAT} = VIH.

2. If there is no address change via $\overline{ADS} = V_{IL}$ (loading a new address) or $\overline{CNTEN} = V_{IL}$ (advancing the address), i.e. $\overline{ADS} = V_{IH}$ and $\overline{CNTEN} = V_{IH}$, then the data output remains constant for subsequent clocks.

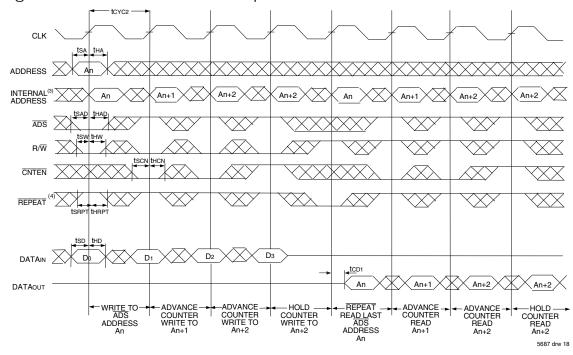
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Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)⁽¹⁾



Timing Waveform of Counter Repeat ^(2,6)



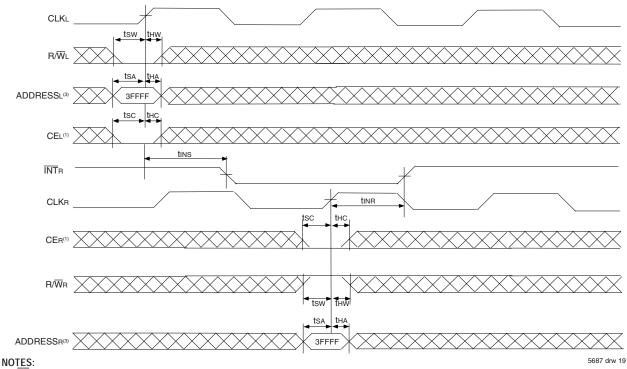
NOTES:

- 1. \overline{CE}_0 , \overline{BE}_n , and $R/\overline{W} = V_{IL}$; CE1 and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{CE}_{0} , $\overline{BE}_{n} = V_{IL}$; $CE_{1} = V_{IH}$.
- 3. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = V_{IL}$ and equals the counter output when $\overline{ADS} = V_{IH}$.
- 4. No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid ADS load will be accessed. For more information on REPEAT function refer to Truth Table II.
- 5. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.
- 6. For Pipelined Mode user should add 1 cycle latency for outputs as per timing waveform of read cycle for pipelined operations.

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Waveform of Interrupt Timing⁽²⁾



- 1. CE0 = VIL and CE1 = VIH
- 2. All timing is the same for Left and Right ports.
- 3. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

		Left Port				Right Port				
CLKL	R/₩L		A17L-A0L ^(3,4)	ĪNTL	CLKr	R/ W R ⁽²⁾	$\overline{CE}R^{(2)}$	A17R-A0R ^(3,4)	ĪNTR	Function
\uparrow	L	L	3FFFF	Х	←	Х	Х	Х	L	Set Right INTR Flag
\uparrow	Х	Х	Х	Х	ŕ	Х	L	3FFFF	Н	Reset Right INTR Flag
\uparrow	Х	Х	Х	L	÷	L	L	3FFFE	Х	Set Left INT∟ Flag
\uparrow	Н	L	3FFFE	Н	ŕ	Х	Х	Х	Х	Reset Left INT∟ Flag
										5687 tbl 13

Truth Table III — Interrupt Flag⁽¹⁾

NOTES:

1. INTL and INTR must be initialized at power-up by Resetting the flags.

2. CE0 = VIL and CE1 = VIH. R/W and CE are synchronous with respect to the clock and need valid set-up and hold times.

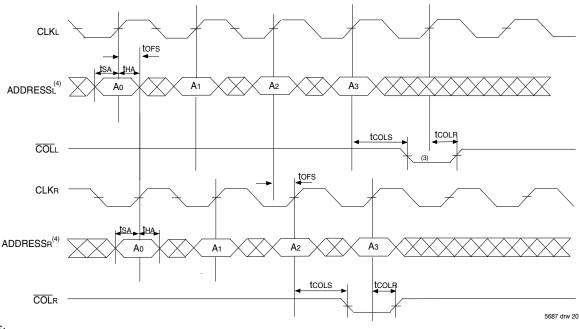
3. A17x is a NC for IDT70T3799, therefore Interrupt Addresses are 1FFFF and 1FFFE.

4. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

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Waveform of Collision Timing^(1,2) Both Ports Writing with Left Port Clock Leading



NOTES:

 $1. \quad \overline{CE}_0 = V_{IL}, \ CE_1 = V_{IH}.$

2. For reading port, OE is a Don't care on the Collision Detection Logic. Please refer to Truth Table IV for specific cases.

3. Leading Port Output flag might output 3tcyc2 + tcoLs after Address match.

4. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

Cycle Time	tors (ns)			
Cycle Tille	Region 1 (ns) ⁽¹⁾	Region 2 (ns) (2)		
5ns	0 - 2.8	2.81 - 4.6		
6ns	0 - 3.8	3.81 - 5.6		
7.5ns	0 - 5.3	5.31 - 7.1		

Collision Detection Timing^(3,4)

56876 tbl 14

NOTES:

1. <u>Region 1</u>

Both ports show collision after 2nd cycle for Addresses 0, 2, 4 etc. 2. Region 2

Leading port shows collision after 3rd cycle for addresses 0, 3, 6, etc. while trailing port shows collision after 2nd cycle for addresses 0, 2, 4 etc.

3. All the production units are tested to midpoint of each region.

4. These ranges are based on characterization of a typical device.

Truth Table IV — Collision Detection Flag

	Left Port						Right Po			
CLKL	R/₩L	ĊĒ∟	A17L-A0L ⁽²⁾		CLKr	R/ W R ⁽¹⁾	$\overline{\text{CE}}_{\text{R}}^{(1)}$	A17R-A0R ⁽²⁾		Function
^	Н	L	MATCH	Н	¢	Н	L	MATCH	Н	Both ports reading. Not a valid collision. No flag output on either port
	Н	L	MATCH	L	¢	L	L	MATCH	Н	Left port reading, Right port writing. Valid collision, flag output on Left port.
^	L	L	MATCH	Н	¢	Н	L	MATCH	L	Right port reading, Left port writing. Valid collision, flag output on Right port.
†	L	L	MATCH	L	¢	L	L	MATCH	L	Both ports writing. Valid collision. Flag output on both ports.

NOTES:

1. CE0 = VIL and CE1 = VIH. R/W and CE are synchronous with respect to the clock and need valid set-up and hold times.

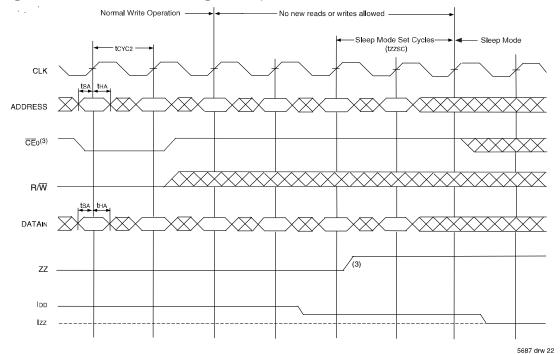
2. Address is for internal register, not the external bus, i.e., address needs to be qualified by one of the Address counter control signals.

5687 tbl 15

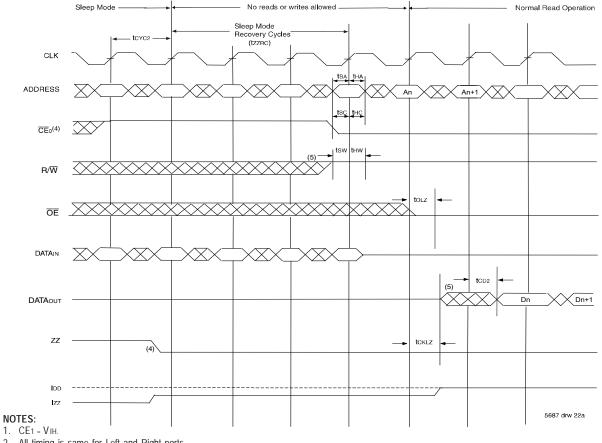
70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Timing Waveform - Entering Sleep Mode (1,2)



Timing Waveform - Exiting Sleep Mode (1,2)



2. All timing is same for Left and Right ports. 3. $\overline{\underline{CE}}_{0}$ has to be deactivated ($\overline{\underline{CE}}_{0} = V_{IH}$) three cycles prior to asserting ZZ (ZZx = V_{IH}) and held for two cycles after asserting ZZ (ZZx = V_{IH}).

- 4. CEo has to be deactivated (CEo = VIH) one cycle prior to de-asserting ZZ (ZZx = VIL) and held for three cycles after de-asserting ZZ (ZZx = VIL).
- 5. The device must be in Read Mode (RW High) when exiting sleep mode. Outputs are active but data is not valid until the following cycle.

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Functional Description

The IDT70T3719/99M provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse width is independent of the cycle time.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on \overline{CE} oor a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70T3719/99Ms for depth expansion configurations. Two cycles are required with \overline{CE} LOW and CE1 HIGH to reactivate the outputs.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (INTL) is asserted when the right port writes to memory location 3FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per the Truth Table I. The left port clears the interrupt through access of address location 3FFFE when $\overline{CEL} = VIL$ and $R/\overline{WL} = VIH$. Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 3FFFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 3FFFF (1FFFF or 1FFFE for 1DT70T3799M). The message (72 bits) at 3FFFE or 3FFFF (1FFFF or 1FFFE for 70T3799M) is user-defined since it is an addressable SRAMlocation. If the interrupt function is not used, address locations 3FFFE and 3FFFF (1FFFF or 1FFFE for 1DT70T3799M) are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

Collision Detection

Collision is defined as an overlap in access between the two ports resulting in the potential for either reading or writing incorrect data to a specific address. For the specific cases: (a) Both ports reading - no data is corrupted, lost, or incorrectly output, so no collision flag is output on either port. (b) One port writing, the other port reading - the end result of the write will still be valid. However, the reading port might capture data that is in a state of transition and hence the reading port's collision flag is output. (c) Both ports writing - there is a risk that the two ports will interfere with each other, and the data stored in memory will not be a valid write from either port (it may essentially be a random combination of the two). Therefore, the collision flag is output on both ports. Please refer to Truth Table IV for all of the above cases.

The alert flag (\overline{COL}_x) is asserted on the 2nd or 3rd rising clock edge of the affected port following the collision, and remains low for one cycle. Please refer to Collision Detection Timing table on Page 19. During that next cycle, the internal arbitration is engaged in resetting the alert flag (this avoids a specific requirement on the part of the user to reset the alert flag). If two collisions occur on subsequent clock cycles, the second collision may not generate the appropriate alert flag. A third collision will generate the alert flag as appropriate. In the event that a user initiates a burst access on both ports with the same starting address on both ports and one or both ports writing during each access (i.e., imposes a long string of collisions on contiguous clock cycles), the alert flag will be asserted and cleared every other cycle. Please refer to the Collision Detection timing waveform on Page 19.

Collision detection on the IDT70T3719/99M represents a significant advance in functionality over current sync multi-ports, which have no such capability. In addition to this functionality the IDT70T3719/99M sustains the key features of bandwidth and flexibility. The collision detection function is very useful in the case of bursting data, or a string of accesses made to sequential addresses, in that it indicates a problem within the burst, giving the user the option of either repeating the burst or continuing to watch the alert flag to see whether the number of collisions increases above an acceptable threshold value. Offering this function on chip also allows users to reduce their need for arbitration circuits, typically done in CPLD's or FPGA's. This reduces board space and design complexity, and gives the user more flexibility in developing a solution.

Sleep Mode

The IDT70T3719/99M is equipped with an optional sleep or low power mode on both ports. The sleep mode pin on both ports is asynchronous and active high. During normal operation, the ZZ pin is pulled low. When ZZ is pulled high, the port will enter sleep mode where it will meet lowest possible power conditions. The sleep mode timing diagram shows the modes of operation: Normal Operation, No Read/Write Allowed and Sleep Mode.

For normal operation all inputs must meet setup and hold times prior to sleep and after recovering from sleep. Clocks must also meet cycle high and low times during these periods. Three cycles prior to asserting ZZ (ZZx = VIH) and three cycles after de-asserting ZZ (ZZx = VIL), the device must be disabled via the chip enable pins. If a write or read operation occurs during these periods, the memory array may be corrupted. Validity of data out from the RAM cannot be guaranteed immediately after ZZ is asserted (prior to being in sleep). When exiting sleep mode, the device must be in Read mode (R/Wx = VIH) when chip enable is asserted, and the chip enable must be valid for one full cycle before a read will result in the output of valid data.

During sleep mode the RAM automatically deselects itself. The RAM disconnects its internal clock buffer. The external clock may continue torun without impacting the RAMs sleep current (Izz). All outputs will remain in high-Z state while in sleep mode. All inputs are allowed to toggle. The RAM will not be selected and will not perform any reads or writes.

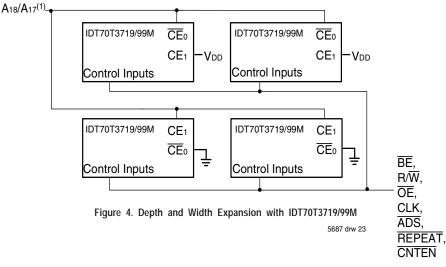
70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Depth and Width Expansion

The IDT70T3719/99M features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70T3719/99M can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 144-bits.



NOTE:

1. A18 is for IDT70T3719, A17 is for IDT70T3799.

JTAG Functionality and Configuration

The IDT70T3719/99M is composed of two independent memory arrays, and thus cannot be treated as a single JTAG device in the scan chain. The two arrays (A and B) each have identical characteristics and commands but must be treated as separate entities in JTAG operations. Please refer to Figure 5.

JTAG signaling must be provided serially to each array and utilize the information provided in the Identification Register Definitions, Scan

Register Sizes, and System Interface Parameter tables. Specifically, commands for Array B must precede those for Array A in any JTAG operations sent to the IDT70T3719/99M. Please reference Application Note AN-411, "JTAG Testing of Multichip Modules" for specific instructions on performing JTAG testing on the IDT70T3719/99M. AN-411 is available at www.idt.com.

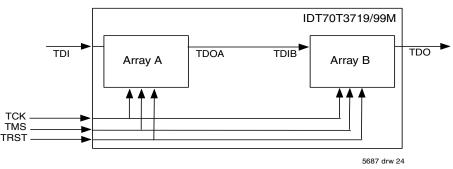
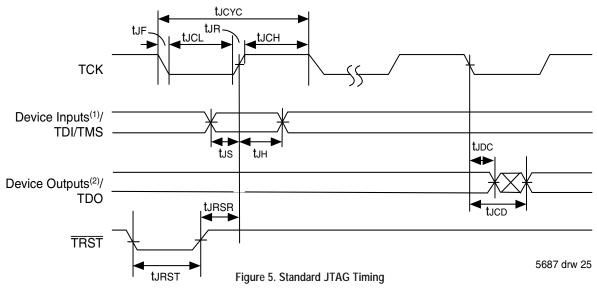


Figure 5. JTAG Configuration for IDT70T3719/99M

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Industrial and Commercial Temperature Ranges

JTAG Timing Specifications



NOTES:

1. Device inputs = All device inputs except TDI, TMS, and TRST.

2. Device outputs = All device outputs except TDO.

		70T3719/99M		
Symbol	Parameter	Min.	Мах.	Units
ticyc	JTAG Clock Input Period	100		ns
исн	JTAG Clock HIGH	40		ns
ticl	JTAG Clock Low	40	_	ns
tjr	JTAG Clock Rise Time		3(1)	ns
IJF	JTAG Clock Fall Time		3(1)	ns
URST	JTAG Reset	50	_	ns
URSR	JTAG Reset Recovery	50		ns
ticd	JTAG Data Output		25	ns
tudo	JTAG Data Output Hold	0	_	ns
tıs	JTAG Setup	15		ns
tн	JTAG Hold	15		ns

JTAG AC Electrical Characteristics^(1,2,3,4)

NOTES:

1. Guaranteed by design.

- 2. 30pF loading on external output signals.
- 3. Refer to AC Electrical Test Conditions stated earlier in this document.
- 4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

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70T3719/99M High-Speed 2.5V 256/128K x 72 Dual-Port Synchronous Static RAM

Industrial and Commercial Temperature Ranges

Identification Register Definitions

Instruction Field Array B	Value Array B	Instruction Field Array A	Value Array A	Description
Revision Number (31:28)	0x0	Revision Number (63:60)	0x0	Reserved for Version number
IDT Device ID (27:12) ⁽¹⁾	0x330	IDT Device ID (59:44) ⁽¹⁾	0x330	Defines IDT Part number
IDT JEDEC ID (11:1)	0x33	IDT JEDEC ID (43:33)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	ID Register Indicator Bit (Bit 32)	1	Indicates the presence of an ID Register

NOTE:

1. Device ID for IDT70T3719M is 0x330. Device ID for IDT70T3799M is 0x331.

Scan Register Sizes

Register Name	Bit Size Array A	Bit Size Array B	Bit Size 70T3719M
Instruction (IR)	4	4	8
Bypass (BYR)	1	1	2
Identification (IDR)	32	32	64
Boundary Scan (BSR)	Note (3)	Note (3)	Note (3)

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System Interface Parameters

Instruction	Code	Description
EXTEST	00000000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	00100010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	01000100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers except \overline{INTx} and \overline{COLx} to a High-Z state.
CLAMP	00110011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	00010001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	01010101, 01110111, 10001000, 10011001, 10101010, 10111011, 11001100	Several combinations are reserved. Do not use codes other than those identified above.
PRIVATE	01100110, 11101110, 11011101	For internal use only.

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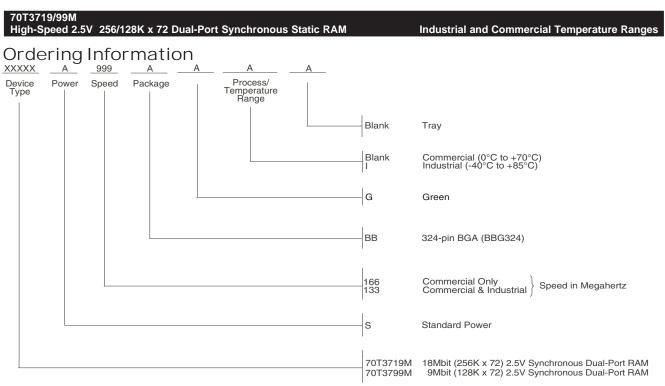
NOTES:

1. Device outputs = All device outputs except TDO.

2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}$.

3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

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Orderable Part Information

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70T3719MS133BBG	BBG324	PBGA	С
166	70T3719MS166BBG	BBG324	PBGA	С

Speed (MHz)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
133	70T3799MS133BBG	BBG324	PBGA	С
	70T3799MS133BBGI	BBG324	PBGA	Ι
166	70T3799MS166BBG	BBG324	PBGA	С

Datasheet Document History:

06/27/05: Initial Datasheet	
07/11/07: Removed Advanced status	
01/19/09: Page 25 Removed "IDT" from orderable part number	
08/06/10: Page 3 Footnote 5 - corrected a typo in the package body and ball-pitch of	dimensions
Page 25 Added Tape & Reel to Ordering Information	
07/15/14: Product Discontinuation Notice - PDN# SP-17-02	
02/14/18: Last time buy expires June 15, 2018	
10/14/19: Page 3 Updated package code	
Page 25 Removed Tape & Reel from Ordering Information	
Page 25 Added Orderable Part Information	
11/04/19: Page 25 Corrected "ns" to "MHz" in the header of the Orderable Part Info	ormation tables

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